



Si4840BDY vs. Si4840DY

Description: N-Channel, 40 V (D-S) MOSFET

Package: SO-8

Pin Out: Identical

Part Number Replacements: Si4840BDY-T1-GE3 replaces Si4840DY-T1-GE3
Si4840BDY-T1-E3 replaces Si4840DY-T1-E3

Table with 5 columns: PARAMETER, SYMBOL, Si4840BDY, Si4840DY, UNIT. Rows include Drain-Source Voltage, Gate-Source Voltage, Continuous Drain Current, Pulsed Drain Current, etc.

Table with 9 columns: PARAMETER, SYMBOL, Si4840BDY (MIN., TYP., MAX.), Si4840DY (MIN., TYP., MAX.), UNIT. Rows include Static parameters like Gate-Threshold Voltage and Dynamic parameters like Total Gate Charge.

Note

a. VGS = 4.5 V for the Si4840BDY; VGS = 5 V for the Si4840DY

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance.